

3 A low V_F MEGA Schottky barrier rectifier Rev. 01 — 21 January 2010

Product data sheet

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Average forward current: I_{F(AV)} ≤ 3 A
- Reverse voltage: $V_R \le 60 V$
- Low forward voltage
- High power capability due to clip-bond technology
- AEC-Q101 qualified
- Small and flat lead SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 1. Quick reference data

 $T_i = 25 \ ^{\circ}C$ unless otherwise specified.

J	· · · · · · · · · · · · · · · · · · ·					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)}	average forward current	square wave; $\delta = 0.5$; f = 20 kHz				
		$T_{amb} \leq 50 ~^{\circ}C$	<u>[1]</u> _	-	3	А
		$T_{sp} \le 135 \ ^{\circ}C$	-	-	3	А
V _R	reverse voltage		-	-	60	V
V _F	forward voltage	I _F = 3 A	-	460	530	mV
I _R	reverse current	V _R = 60 V	-	80	200	μA

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



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2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	e Graphic symbol
1	cathode	[1]	
2	anode	1	1 🕂 2
			sym001

[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information					
Type number Package					
	Name	Description	Version		
PMEG6030EP	-	plastic surface-mounted package; 2 leads	SOD128		

4. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG6030EP	AB

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0, (,		
Symbol	Parameter	Conditions	Min	Max	Unit
V _R	reverse voltage	T _j = 25 °C	-	60	V
I _{F(AV)}	average forward current	square wave; $\delta = 0.5$; f = 20 kHz			
		$T_{amb} \leq 50 ~^{\circ}C$	<u>[1]</u>	3	А
		$T_{sp} \le 135 \ ^{\circ}C$	-	3	А
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	[2] _	50	A
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[3][4]</u>	625	mW
			[3][5]	1050	mW
			[3][1]	2100	mW

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Table 5.	Limiting	values	continued
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In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

[2] $T_j = 25 \ ^\circ C$ prior to surge.

[3] Reflow soldering is the only recommended soldering method.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1][2]			
	junction to ambient		[3] _	-	200	K/W
			[4] _	-	120	K/W
			[5] _	-	60	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[6]</u> _	-	12	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

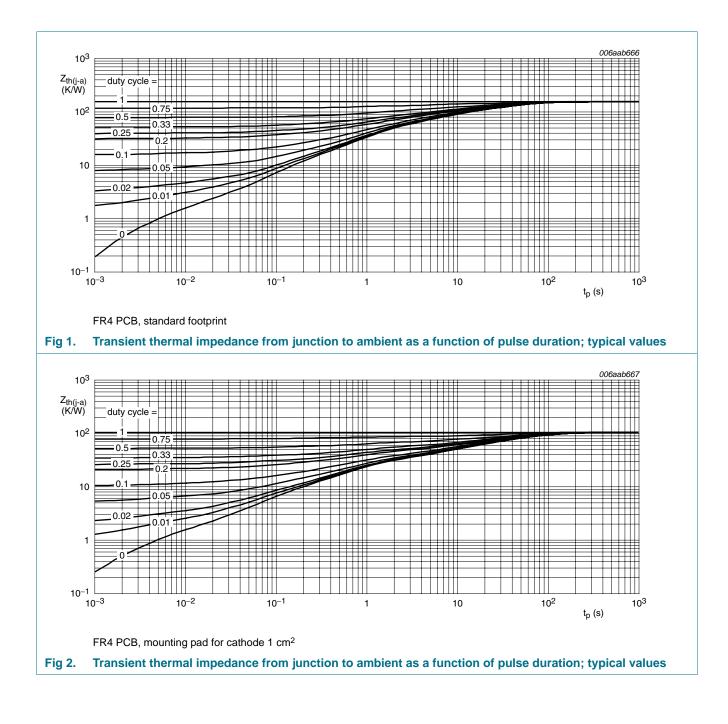
[5] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.

[6] Soldering point of cathode tab.

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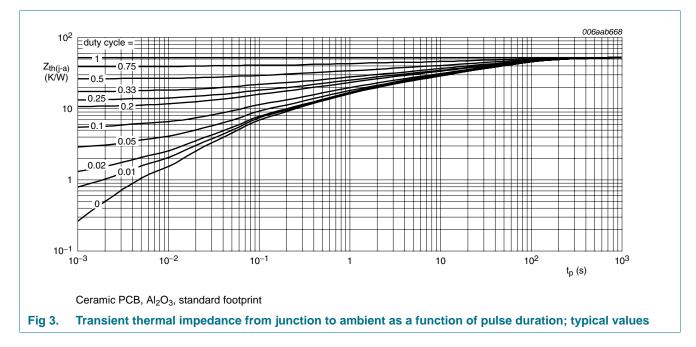
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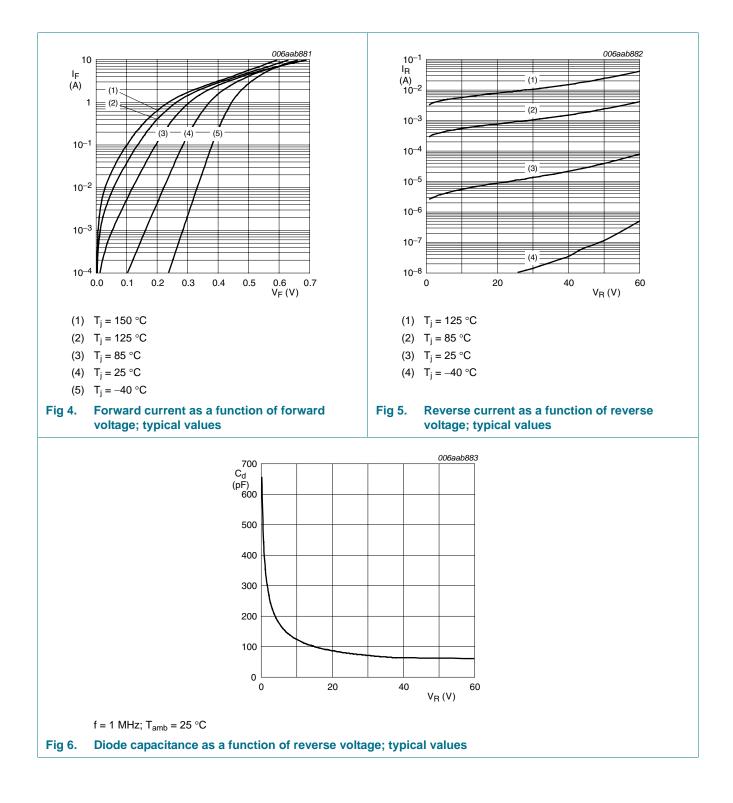


7. Characteristics

Table 7.Characteristics

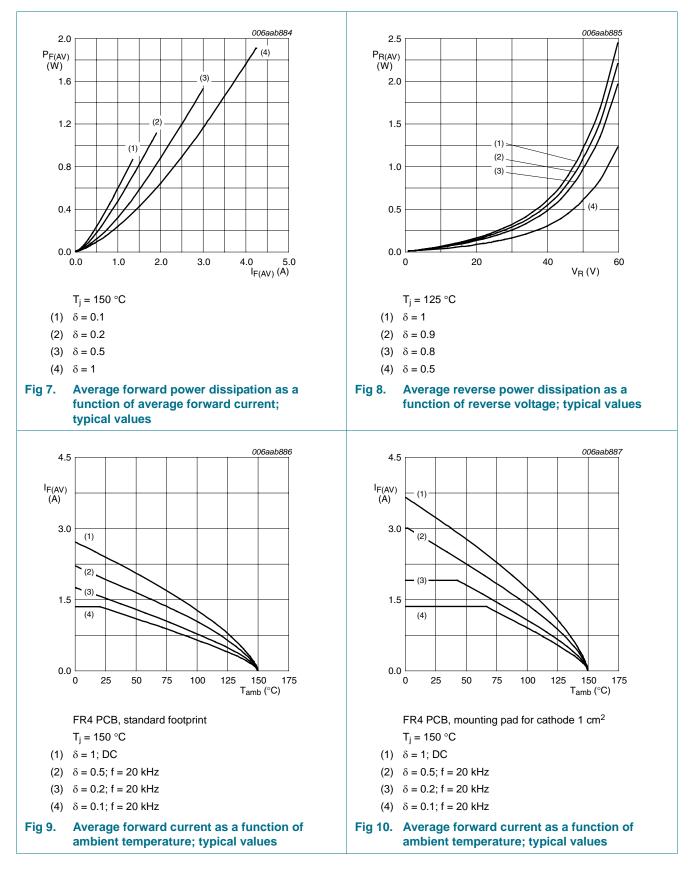
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VF	forward voltage	I _F = 0.1 A	-	290	330	mV
		I _F = 0.5 A	-	340	400	mV
		I _F = 1 A	-	380	440	mV
		I _F = 1.5 A	-	400	470	mV
		I _F = 2 A	-	430	500	mV
		I _F = 3 A	-	460	530	mV
I _R	reverse current	$V_R = 5 V$	-	4	-	μA
		V _R = 10 V	-	5	-	μA
		V _R = 60 V	-	80	200	μA
C _d	diode capacitance	f = 1 MHz				
		$V_R = 1 V$	-	360	-	pF
		V _R = 10 V	-	120	-	pF

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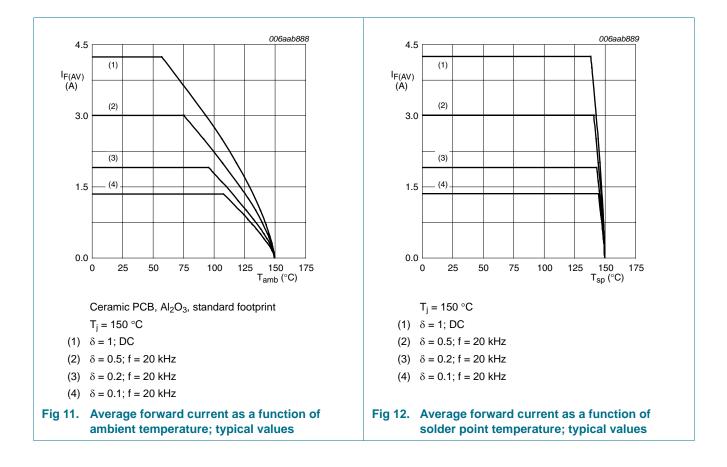
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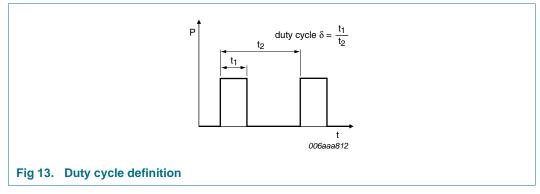
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8. Test information

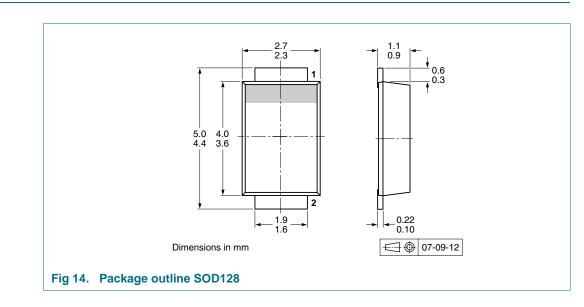


The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current,

 $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.



9. Package outline

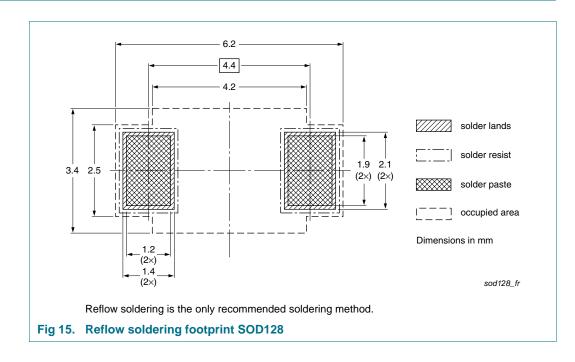
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10. Packing information

Table 8. Packing methods The indicated -xxx are the last three digits of the 12NC ordering code.[1]					
Type number Package Description Packing quantity					
			3000		
PMEG6030EP	SOD128	4 mm pitch, 12 mm tape and reel	-115		

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

11. Soldering



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12. Revision history

Table 9. Revision hist	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PMEG6030EP_1	20100120	Product data sheet	-	-			

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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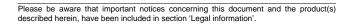
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Date of release: 21 January 2010 Document identifier: PMEG6030EP_1

